

Amendments to the Drawings:

The attached replacement drawing sheet makes changes to Figs. 15-17 and replaces the original sheet with new Figs. 15-17

Attachment: Replacement Sheet

REMARKS

Claims 1-17 are pending in this application. By this Amendment, Figs. 15-17 are replaced with new Figs. 15-17, claim 1 is amended and new claims 16 and 17 are added.

Claims 6, 7 and 12-14 have been withdrawn.

The Office Action objects to Figs. 15-17. Figs. 15-17 have been replaced by new Figs. 15-17 which are designated as "Related Art." Withdrawal of the objection is respectfully requested.

The Office Action rejects claims 1-5, 8-11 and 15 under 35 U.S.C. §102(b) over U.S. Patent No. 6,011,275 to Ohtani et al. This rejection is respectfully traversed.

The Office Action asserts that pattern 410 formed from crystalline silicon film 408 is a monocrystalline semiconductor layer. Specifically, the Office Action asserts that Ohtani discloses that layer 408 is a crystalline silicon having a singular crystal structure at col. 6, lines 14-20 or col. 14, lines 1-2, and thus is monocrystalline. However, at col. 11, lines 39-48, Ohtani recites that crystalline film 408 includes a plurality of slender cylindrical crystals.

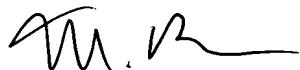
Furthermore, the recitation of col. 14, lines 1-2 refers to "the thin film transistor employing the crystalline silicon film having the above singular crystal structure." This recitation clearly refers to crystalline silicon film 408, which has a plurality of crystals. Thus, Ohtani does not disclose a transistor comprising at least a monocrystalline semiconductor layer as in claim 1.

A monocrystalline semiconductor layer has no grain boundaries, because the entire film is formed as a single crystal grain. Because the slender cylindrical crystal of Ohtani's crystalline silicon film 408 are "aligned in parallel through a plurality of grain boundaries" the crystalline silicon film 408 is obviously not a monocrystalline semiconductor layer.

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 1-17 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



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JAO:MB/kzb

Attachment:

Replacement Drawing Sheets

Date: July 15, 2005

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